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最新トランジスタ規格表 (New Transistor Manual) lists all the transistors registered with the Electronic Industries Association of Japan (EIAJ), arranged in a manner easy to look up. We hope that you will make full use of the data provided in this manual by referring to the Japanese-English translation key given below.

型名	社名	用途	構造	最大定格 (T _b =25°C)					電気的特性 (T _b =25°C)										外形	備考
				V _{ceo} (V)	V _{ceo} (V)	I _c (mA)	P _c (mW)	T _j (°C)	I _{ceo} 最大値 (μA)	直流又はパルスI _{BE}		バイアス		h _{FE}	h _{FE} h _{FE} * (Ω)	h _{FE} h _{FE} * (×10 ⁻⁴)	h _{FE} h _{FE} * (μS)	f _{αB} f _r * (Mc)		
1	2	3	4	5					6		7		8				9	10	11	12

- 1 TYPE NUMBER
- 2 ORIGINAL MANUFACTURER
- 3 USES
- 4 MATERIAL AND STRUCTURE
- 5 MAXIMUM RATINGS
- 6 I_{CBO} MAXIMUM VALUE AND V_{CB} VALUE (CRITERIA FOR MEASURING I_{CBO})
- 7 STANDARD VALUE OF DC/PULSE h_{FE} AND V_{CE}, I_C (CRITERIA FOR MEASURING DC/PULSE h_{FE})
- 8 STANDARD VALUE OF h PARAMETERS AND BIAS V_{CB}, I_E (CRITERIA FOR MEASURING h PARAMETERS)

- * INDICATES VALUE IN GROUNDED-BASE OPERATION, OTHERWISE VALUE IN EMITTER-GROUNDED OPERATION.
- 9 f_{αB} OF RF CHARACTERISTIC, EXCEPT IN CASE OF * WHICH INDICATES VALUE OF f_r.
- 10 C_{ob} AND r_{bb'} OF RF CHARACTERISTICS EXCEPT IN CASE OF * IN r_{bb'} COLUMN WHICH INDICATES VALUE OF h_{ie} (real)
- 11 OUTLINE
- 12 REMARKS

:とコンプリ: COMPLEMENTARY TO

型名	社名	用途	構造	最大定格 ($T_a = 25^\circ\text{C}$)					電 気 的 特 性 ($T_a = 25^\circ\text{C}$)											外形	備考		
				V_{CB0} (V)	V_{E0} (V)	I_C (mA)	P_C (mW)	T_j ($^\circ\text{C}$)	I_{CBO} 最大値		直流又はパルス h_{FE}		バイアス		h_{fe} $h_{j\beta}$ *	h_{ie} $h_{i\beta}$ *	h_{re} $h_{r\beta}$ *	h_{oe} $h_{o\beta}$ *	f_{β} f_T *			C_{ob} (pF)	r_{ob} $h_{ie}(\text{real})$ *
									(μA)	$V_{CB}(\text{V})$	$V_{CE}(\text{V})$	$I_C(\text{mA})$	$V_{CB}(\text{V})$	$I_E(\text{mA})$									
2SC2292	新電元	SW	Si.T	500	7	8 A	80W ($T_c=25^\circ\text{C}$)	150	100	500	20	2	4 A	10	-1 A	$t_{on} < 1\mu\text{S}$, $t_{off} < 3\mu\text{S}$		20 *			102	T8M40F1	
" 2293	"	"	"	500	7	10 A	100W ($T_c=25^\circ\text{C}$)	150	100	500	20	2	5 A	10	-1 A	$t_{on} < 1\mu\text{S}$, $t_{off} < 3\mu\text{S}$		20 *			102	T10M40F1	
" 2294	松下	RF	Si.EP	30	5	30	250	125	1	10	100	10	1	10	-1			200 *	2	20	138		
" 2295	"	"	"	30	5	30	200	125	0.1	10	50-220	10	1	10	-1			>150 *	$C_{rr} 0.9$	$Z_{rb} 22$	176	2SA1022 とコンプリ	
" 2296	"	"	"																				
★ " 2297	日立	PA	Si.E	55	4	8 A	25W ($T_c=25^\circ\text{C}$)	150	0.1	45	100	10	2 A	10	-150	$P_o > 16\text{W}$, $(f=27\text{MHz}, \eta > 60\%$ $V_{cc}=12\text{V}, P_i=1\text{W})$		130 *	140	0.4	268		
" 2298	"	RF	"	30	10	1 A	8 W ($T_c=25^\circ\text{C}$)	150	10	30	>4000	3	400								160	チーリントン	
★ " 2299	富士通	"	Si.EP	20	5	1 A	500	150	0.5	15	200	5	10	5	-10			150 *	10	15 *	138		
" 2300	"	"	"	50	5	1 A	500	150	0.5	40	200	5	10	5	-10			150 *	10	15 *	138		
" 2301	日電	PA	Si.E	45	2	2.8 A	46W ($T_c=25^\circ\text{C}$)	200	2 mA	30	30	10	2 A			$P_o=16\text{W}$ $(f=890\text{MHz}, V_{cc}=18\text{V}, P_i=3.6\text{W})$						164	
" 2302	サンケン	SW	Si.T	500	10	7 A	40W ($T_c=25^\circ\text{C}$)	150	100	500	15	4	5 A			$t_{on} < 1.3\mu\text{S}$, $t_{off} < 3.5\mu\text{S}$						100	
" 2303	"	"	"	500	10	7 A	80W ($T_c=25^\circ\text{C}$)	150	100	500	15	4	5 A			$t_{on} < 1.3\mu\text{S}$, $t_{off} < 3.5\mu\text{S}$						102	
" 2304	"	"	"	500	10	12 A	100W ($T_c=25^\circ\text{C}$)	150	100	500	15	4	10 A			$t_{on} < 1.3\mu\text{S}$, $t_{off} < 3.5\mu\text{S}$						102	
" 2305	"	"	"																				
" 2306	サンケン	SW	Si.TMe	450	6	15 A	150W ($T_c=25^\circ\text{C}$)	150	1mA	450	>10	4	5 A	12	-500	$t_r=0.35\mu\text{S}$, $t_{off}=2.1\mu\text{S}$		7 *				102	
" 2307	"	"	"																				
" 2308	日立	AF	Si.E	55	5	100	200	125	0.5	18	100-320	12	2	12	-2			230 *	1.8		138	2SA1030 とコンプリ	
" 2309	"	"	"	55	5	100	200	125	0.5	18	250-1200	12	2	12	-2			230 *	1.8		138		
" 2310	"	LN	"	55	5	100	200	125	0.5	18	100-320	12	2	12	-2	$NF=3\text{dB}$ $(6\text{V}, 0.1\text{mA}, 120\text{Hz})$		230 *	1.8		138	2SA1032 とコンプリ	
" 2311	富士通	SW	Si.EP	50	5	1 A	1 W	150	0.5	40	55	1	500			$t_{on}=45\text{nS}$, $t_{off}=90\text{nS}$ $t_{tr}=70\text{nS}$				<12	328		
" 2312	"	"	"																				
" 2313	三菱	PA	Si.EP	40	4	10 A	60W ($T_c=25^\circ\text{C}$)	175	1mA	25	50	10	1 A			$P_o=38\text{W}$ $(f=65\text{MHz}, V_{cc}=12\text{V}, P_i=3.5\text{W})$						323	
" 2314	三洋	RF.PA	"	75	5	1 A	5 W ($T_c=25^\circ\text{C}$)	150	1	40	60-320	5	500	10	-50	$P_o=1.8\text{W}$, $\eta > 60\%$ $(f=27\text{MHz}, V_{cc}=12\text{V}, P_i=35\text{mW})$		250 *	15		296		
" 2315	サンケン	PA	Si.TMe	80	6	6 A	50W ($T_c=25^\circ\text{C}$)	150	100	80	800	4	500	12	-500			30 *	140	20	298		
" 2316	"	"	"	100	6	6 A	50W ($T_c=25^\circ\text{C}$)	150	100	100	800	4	500	12	-500			30 *	140	20	298		
" 2317	"	"	"	200	6	1 A	30W ($T_c=25^\circ\text{C}$)	150	100	200	1000	4	200	12	-100			30 *	45	45	298		
" 2318	東芝	"	Si.EP	40	3.5	350	3.5W ($T_c=25^\circ\text{C}$)	175	1	30	30-180	5	100	10	-90	$G_{11}=16\text{dB}$ $(10\text{V}, 90\text{mA}, 250\text{MHz})$		2700 *	2.9		85B		
" 2319	"	"	"	40	3.5	350	5 W ($T_c=25^\circ\text{C}$)	175	1	30	30-180	5	100	10	-90	$G_{11}=16\text{dB}$ $(10\text{V}, 90\text{mA}, 250\text{MHz})$		2900 *	3.5		270		
" 2320	三菱	AF	Si.E	50	6	200	300	125	0.1	50	90-800	6	1	6	-10	$NF < 15\text{dB}$ $(6\text{V}, 0.1\text{mA}, 1\text{kHz})$		200 *	3.5		138		
★ " 2321	富士通	RF.AF	Si.EP	130	4.5	8 A	80W ($T_c=25^\circ\text{C}$)	150	50	130	100	5	500	10	-1 A			60 *	250		102	2SA1001 とコンプリ	